

Prof. Ohmi's Paper

January–December, 1999

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- E816 (C) T. Kezuka, F. Kamiya, M. Itano, and T. Ohmi, "The Behavior of Surfactant Adsorption and Minimization of Particle Contamination in HF Solution," 1999 Semiconductor Pure Water and Chemicals Conference, pp. 337-354, Santa Clara, March 1999.
- E817 (F) Tetsuya Yamamoto, Nguyen Thang Chien, Makoto Ando, Naohisa Goto, Masaki Hirayama, and Tadahiro Ohmi, "Design of Radial Line Slot Antennas at 8.3 GHz for Large Area Uniform Plasma Generation," Jpn. J. Appl. Phys., Vol. 38, Part 1, No. 4A, pp. 2082-2088, April 1999.
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